

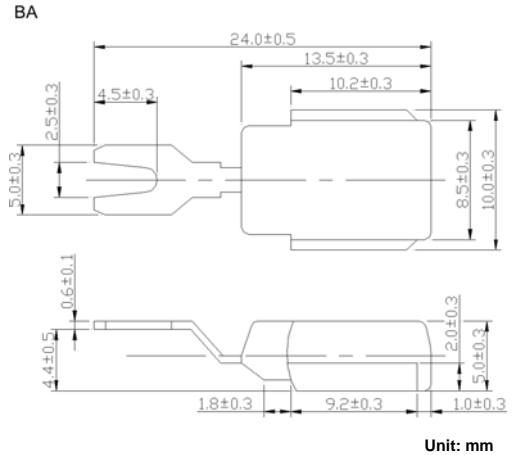
Technical Specification:

Features:

- ◆ High power capability
- ◆ Economical
- ◆ Avalanche Voltage: 24V to 32V

Mechanical Data:

- ◆ Copper cup with transfer molded plastic
- ◆ Epoxy: UL94-0 rate flame retardant
- ◆ Polarity: GBA35Z-P lead-P
GBA35Z-N lead-N
- ◆ Glass passivated chip or oJ chip
- ◆ Technology vacuum soldered
- ◆ Lead: Plated lead, solderable per MIL-STD-202E method 208C
- ◆ Weight: 0.094 ounces, 2.65 grams



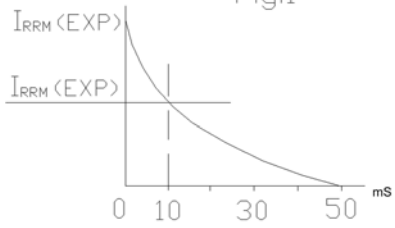
Maximum Ratings and Electrical Characteristics

- ◆ Rating at 25°C ambient temperature unless otherwise specified.
- ◆ Single phase, half wave, 60Hz, resistive or inductive load.
- ◆ For capacitive load derate current by 20%.

Parameters	Symbols	GBA35Z-P /GBA35Z-N			Units
		Min.	Nominal	Max.	
DC peak repetitive reverse voltage	V_{RRM}		20		Volts
Working peak reverse voltage	V_{RHM}		20		
DC blocking voltage	V_R		20		
Average rectified forward current at $T_c=125^\circ\text{C}$	I_T		35		Amps
Repetitive peak reverse surge current $T_c=80\text{m sec duty cycle } <1\%$	I_{TSM}		35		Amps
Breakdown voltage (V_{BR} @ $I_F=100\text{mA}$)	V_{BR}	24	25 / 27	32	Volts
$I_F=90\text{Amps}, T_c=150^\circ\text{C}, PW=80\text{usec}$	V_{BR}			40	
Forward voltage drop (V_{sd}) @ $I_F=100\text{Amps} < 300\text{usec}$	V_F	0.98	1.05	1.10	Volts
Peak forward surge current	I_{FSM}		400		Amps
Reverse leakage ($I_R=20\text{Vdc}$) $T_A=25^\circ\text{C}$	I_R	0.2	1.0	2.0	μA
Operating and storage junction temperature range	T_J, T_{STG}	-65 to +175			$^\circ\text{C}$

Notes: 1. Enough heatsink must be considered in application.

Fig.1



Surge current characteristics